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Peculiar behavior of the electrical resistivity of MnSi at the ferromagnetic phase transition

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The electrical resistivity of a single crystal of MnSi was measured across its ferromagnetic phase transition line at ambient and high pressures. Sharp peaks of the temperature coefficient of resistivity characterize the transition line. Analysis of these data shows that at pressures to ~ 0.35 GPa these peaks have fine structure, revealing a shoulder at ~ 0.5 K above the peak. It is symptomatic that this structure disappears at pressures higher than ~ 0.35 GPa, which was identified earlier as a tricritical point.

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The intermetallic compound MnSi experiences a second order phase transition at temperature T_c slightly below 30 K, acquiring helical magnetic structure and becoming a weak itinerant ferromagnet. On application of pressure the transition temperature T_c decreases and tends to zero at a pressure of about 1.4 GPa [1]. As was noticed for the first time in ref. [2] (see also [3]), a λ-type singularity of the AC magnetic susceptibility χ_{AC} at the phase transition in MnSi deforms gradually with pressure and becomes a simple step at pressures more than 1GPa. That was ground to claim existence of a tricritical point with the coordinates: ~ 1.2 GPa, ~ 12 K [2, 3]. This conclusion was partly disputed in ref. [4], where new measurements of χ_{AC} of MnSi at high pressures, created by compressed helium, were reported. These authors [4] confirmed the existence of a tricritical point on the phase transition line in MnSi but placed it at much lower pressure and at significantly higher temperature ($P_{tr} \cong 0.355$ GPa, $T_{tr} \cong 25.2$ K).

To resolve that somewhat controversial issue we have carried out precise resistivity measurements of a MnSi single crystal across the phase transition line at ambient and at high pressures, using a compressed helium technique. The primary purpose was to study behavior of the temperature coefficient of resistivity $d\rho/dT$ at the transition line. According to the theoretical conclusions [5, 6, 7], a temperature coefficient of resistivity diverge at a second order magnetic phase transition and can be characterized by a static critical exponent . Contrary to our expectations, we found that peaks in $d\rho/dT$ at T_c are accompanied by a well-defined shoulder on their high temperature side, which vanish when approaching a pressure ~ 0.35 GPa. This finding nicely correlates with corresponding features in ultrasound attenuation [8], thermal expansion [9], and heat capacity [10], discovered in the critical region of MnSi at ambient pressure.

The single crystal of MnSi was grown from a tin flux by dissolving pre-alloyed Mn and Si in excess Sn. For resistivity measurements, four Pt-wires of 25-μm in diameter were welded to the crystal with dimensions of about $0.5\times0.3\times0.3 mm^3$. The temperature of the magnetic phase transition T_c and resistivity ratio $R_{300}/R_{(T=2.1)}$, taken at ambient pressure, are equal to 29.25 ± 0.02 K and ≈ 100 correspondingly. The crystal was placed into a high pressure cell made of beryllium copper. Fluid and solid helium were used as a pressure medium. Temperature was measured by a calibrated Cernox sensor, imbedded in the cell body, with an accuracy of about 0.05 K. A calibrated manganin gauge was used to measure pressure with accuracy about 10^{-3} GPa in the fluid helium domain. In the domain of solid helium, pressure was calculated on the basis of the measured helium-crystallization temperatures and data for the equation of state of helium. Accuracy of pressure measurements in solid helium is estimated as 5×10^{-3} GPa. The resistivity was measured by a four-terminal DC method. The experimental setup, including the high pressure gas installation and the cryostat, is described in [4], [11].

The resistivity measurements of MnSi were carried out along 24 quasi isobars [12] in the pressure range from zero to 1.5 GPa. Selected experimental data are displayed in Fig.1. We have tried to describe the resistivity curves in the temperature range from zero to the phase transition region by various polynomials that contained potentially important T^2 and/or T^5 terms accounting for scattering by spin and density fluctuations (phonons) [13, 14]. The overall results appeared to be quite satisfactory though we observed small but systematic deviations of the experimental data points from the corresponding approximations at low temperatures. Replacing the T^2 term with T^n improves the situation but does not correct it entirely, though always leads to a value of $n < 2$. On the other hand, as is seen in Fig.1 the pressure derivatives of resistivity are positive below the Curie point and negative above (see also [3]). This implies a dominant role of order parameter fluctuations in the electron scattering in MnSi. Hence, any analysis of the resistivity behavior in MnSi should take into account this significant factor. We will discuss this issue elsewhere. However, it is important to emphasize here that the residual resistivity of

MnSi, derived from reasonable extrapolations, decreases monotonically from 2.25 to 2.11 $\mu\Omega$cm over all the pressure range studied on compression. This indicates that many cycles of pressure loading and unloading, cooling and warming do not introduce additional defects into the sample. The temperature-dependent resistivity of MnSi above the phase transition line shows clear signs of resistivity saturation at $T \rightarrow \propto$ [15].

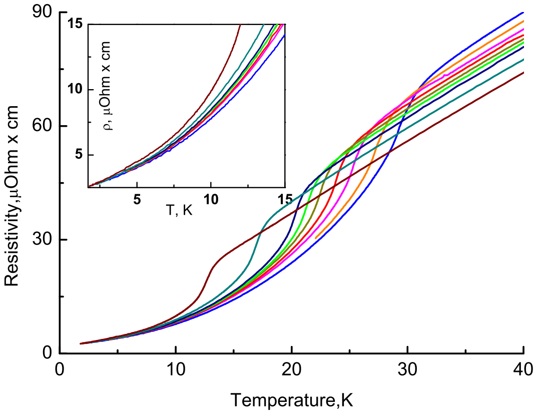

FIG. 1: (Color online) Temperature dependence of the electrical resistivity $\rho(T)$ of MnSi at different pressures. The isobars correspond to pressures in GPa: 0, 0.2, 0.32, 0.43, 0.54, 0.63, 0.7, 0.885, 1.13, counting from the right to the left at the bottom of the figure.

Now we turn to an analysis of the temperature coefficient of resistivity $d\rho/dT$ in the vicinity of the phase transition boundary. Temperature derivatives of resistivity ρ were taken by averaging the slopes of two adjacent points of the raw experimental data. The outcome of this procedure is illustrated in Fig.2, where also the smoothing lines are shown. As is seen from the figure at ambient pressure the curve $\frac{d\rho}{dT}(T)$ has a distinct shoulder on the high temperature side of T_c which disappears at high pressure. The evolution of the shape of the peaks of $d\rho/dT$ with applied pressure is shown in Fig.3. The shoulder in $\frac{d\rho}{dT}(T)$ vanishes at a pressure of around 0.35 GPa that was recognized early as a coordinate of the tricritical point [4]. The overall trend is that at low pressure structure in $d\rho/dT$ consists of two components: one sharp and another broad, separated only by half a degree or so. Because of lack of *a priori* knowledge of the peak forms and uncertainty with background subtraction, we could not separate these peaks in a reliable way. The obvious overlapping of the peaks makes also unreliable attempts to obtain a critical exponent, based on behavior $d\rho/dT$ [5, 6, 7]. Nevertheless, we have found that an approximation of $d\rho/dT$ at $T < T_c$ with the expression

$$\frac{d\rho}{dT} = a + bT + c(T_c - T)^{-m} \qquad (1)$$

gives $m \approx 0.25$ in case of the low pressure isobars, which is a reasonable value for an exponent characterizing critical behavior of heat capacity near helical spin ordering [16, 17]. At pressures more than 0.3-0.4 GPa, the fitting became unstable and did not lead to realistic values of the exponents.

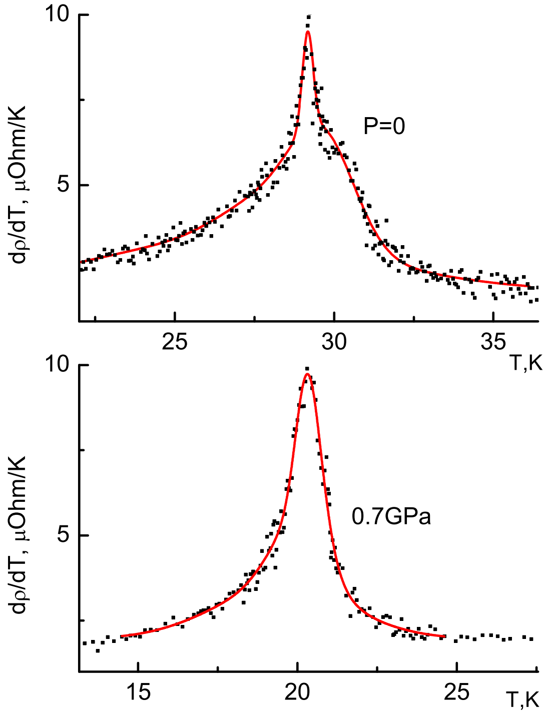

FIG. 2: (Color online) Examples of temperature derivatives of resistivity $d\rho/dT$ at ambient and elevated pressures. The square dots are the temperature derivatives of resistivity, taken by averaging the slopes of two adjacent points of the raw experimental data. The solid lines are results of smoothing procedures.

Summarizing, we point out that the reported experimental data demonstrate complicated behavior of the temperature coefficient of resistivity of MnSi in the vicinity of its phase transition. As is seen from Fig.3, $d\rho/dT$ evolves from a highly asymmetric, not quite resolved doublet with one rather sharp component at ambient pressure to the single, fairly symmetric peak at pressure, corresponding to the tricritical point. It was mentioned earlier that a doublet structure of related peaks was discovered in sound absorption [8], thermal expansion [9], and heat capacity [10] at the phase transition in MnSi that correlate with the current observations. Unfortunately, little is known about the origin of this structure, but what we know is that the high temperature satellite does not reveal itself in magnetic susceptibility measurements [3, 4]. The data comparison shows that the magnetic transition is associated with a sharp peak on the low

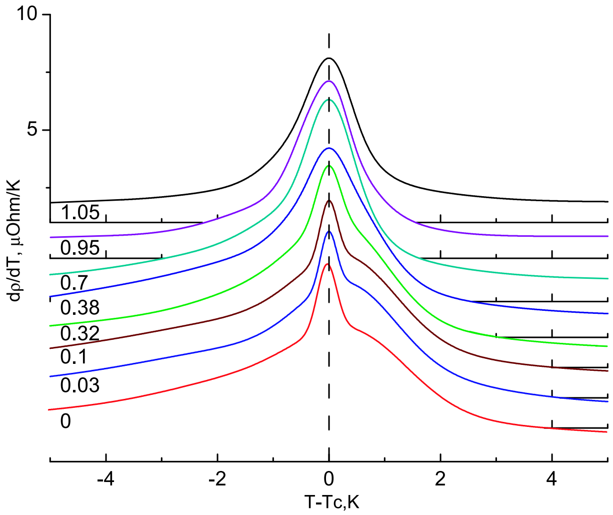

FIG. 3: (Color online) Evolution of temperature derivatives of resistivity $d\rho/dT$ with pressure. The pressures in GPa are shown at the left side of the figure.

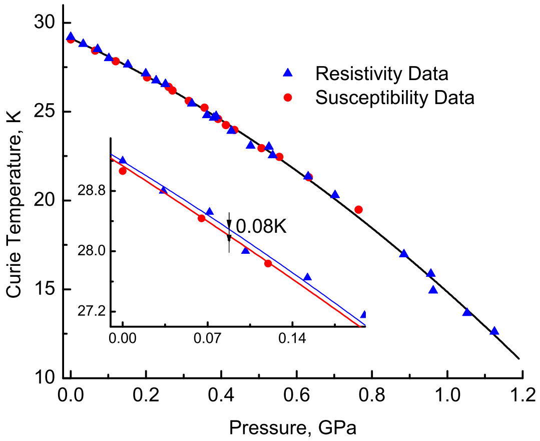

FIG. 4: (Color online) Pressure dependence of the Curie temperature of MnSi according to the current resistivity measurements and the AC susceptibility data [4]. The inset shows that the average mismatch of the two sets of the data is less than 0.1K.

temperature side of $d\rho/dT$ (Fig.4). Thus, the observed shoulder in $d\rho/dT$ could be connected with short range spin order or with the spin texture [19, 20]. However, it does not appear that the shoulder in $d\rho/dT$ marks any kind of a conventional phase transition. Nevertheless, one cannot exclude that a topological phase transition takes place at a temperature above the magnetic transformation. In the latter case, instead of a tricritical point there would be a special kind of a multicritical point in the phase diagram of MnSi. But, if the scenario with a topological phase transition is not appropriate, then the shoulder in $d\rho/dT$ disappears, being adsorbed by the volume instability gap, which is opened at a tricritical point [21].

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